

# caeleste



ICSO 2014  
Tenerife

## CRYOGENIC AND RADIATION-HARD ASIC FOR INTERFACING LARGE FORMAT NIR/SWIR DETECTOR ARRAYS

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# About us

- **Image sensors and periphery ASICs**
- **Founded 2006**
- **Mechelen, Belgium**
- **17 p (10 designers)**



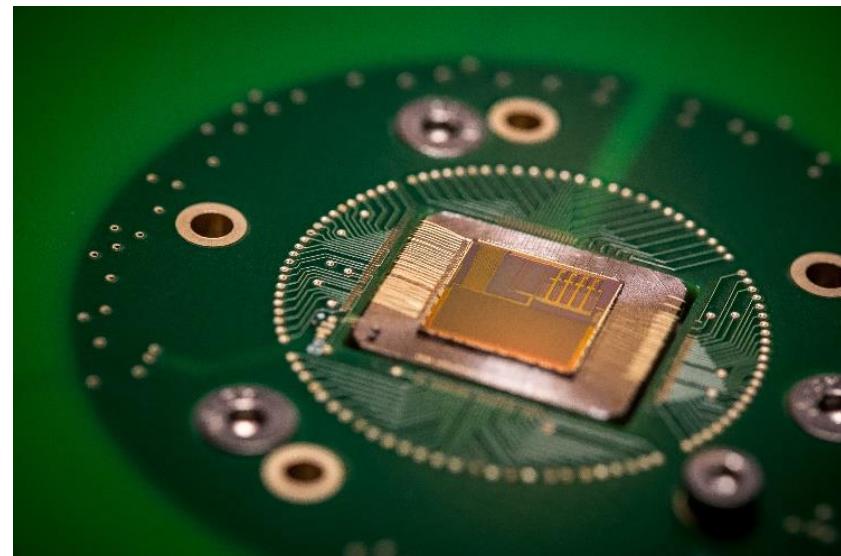
Supplier of Custom designed  
Beyond “State of the Art” CMOS Image sensors and ASIC for  
**Space, Scientific, Industrial and Medical** applications

# Outline

- **Motivation**
- **Architecture and building block design**
- **Design for Radiation hardness and Cryogenic temperature**
- **Test results**
- **Conclusions & future work**

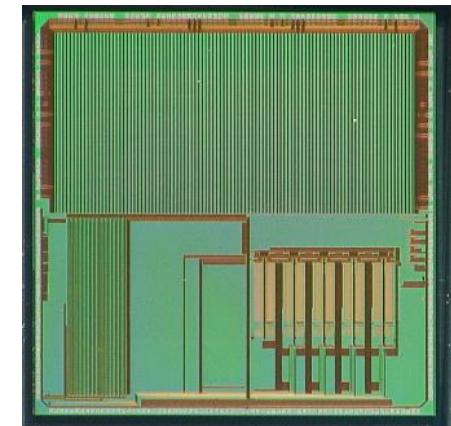
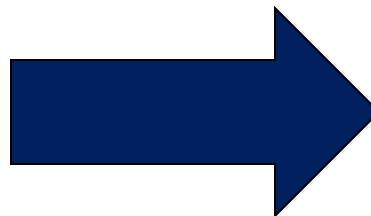
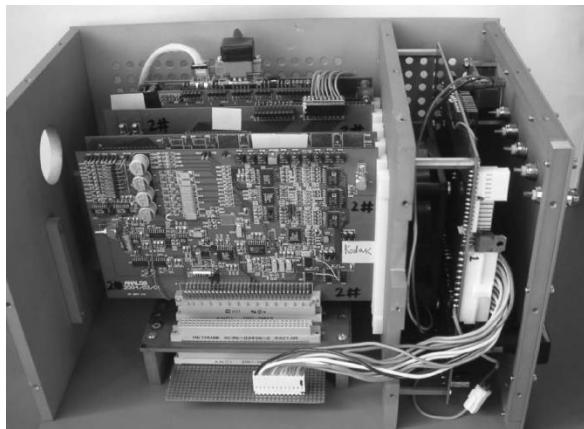
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# Why an ASIC ?

To operate an IR imagers



[Z.Zhao.SDA'05]

## Analog domain

- Signal conditioning
- Analog to digital converter
- Regulated power supply
- Bias voltage/current references

## Digital domain

- Digital control core
- Memory & Clock
- Data Communication

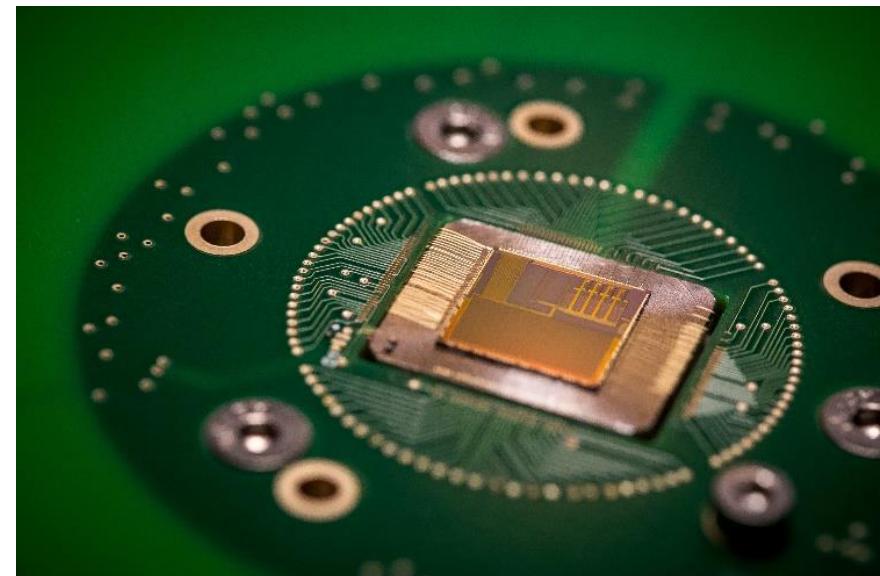
# The ASIC

This development aims at providing the community with a IR imager accompany ASIC

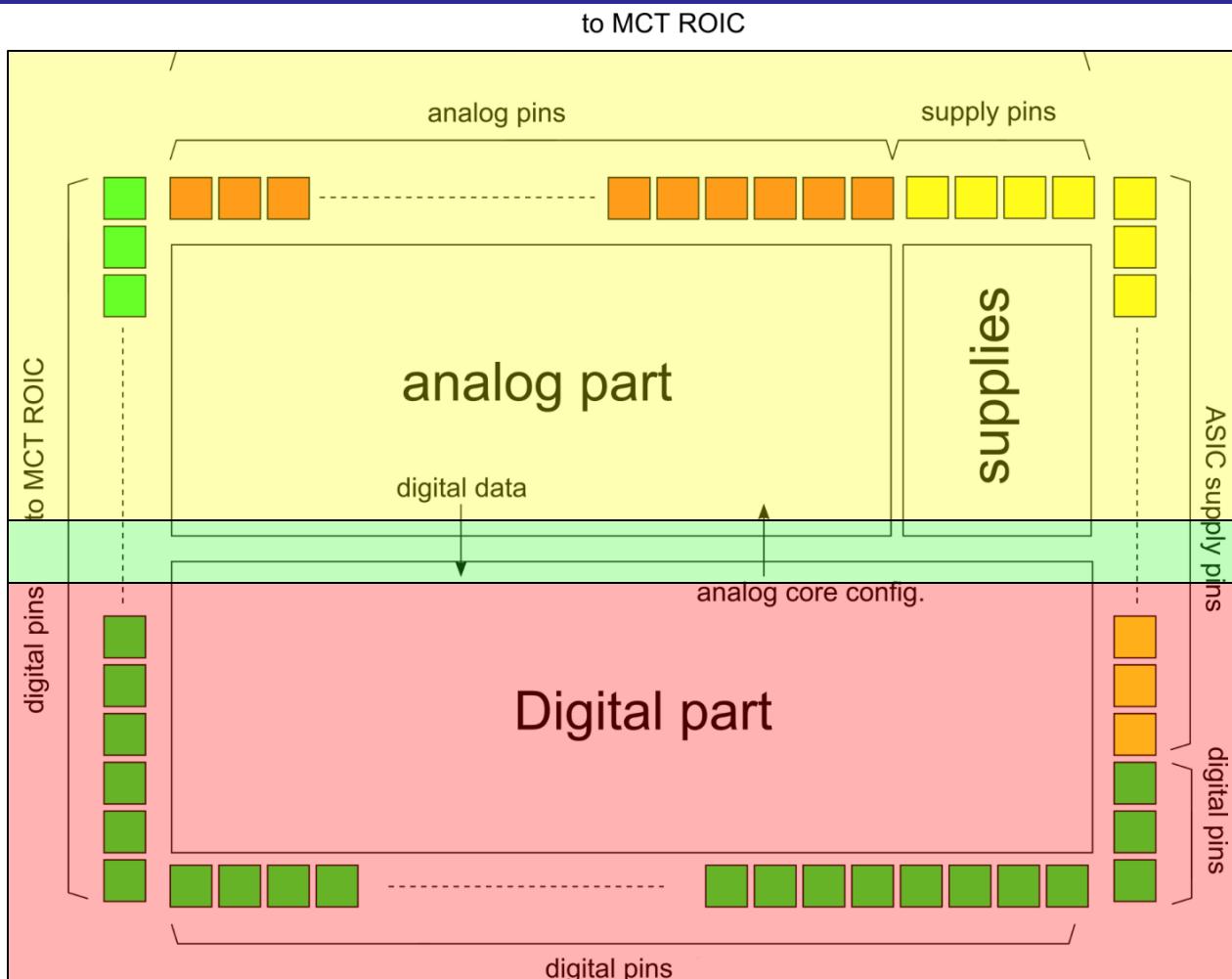
- Tailored to imagers (especially IR sensor)
  - Easy to control
  - Simple to intergrade
- Taking in consideration multiple IR detector manufacturers specificities
- Wide operating temperature range (77k – room T)
- Able to drive multi-sensor/array systems
- Radiation hard
  - 1Mrad TID
  - 60MeVcm<sup>2</sup> /mg SEU

# Outline

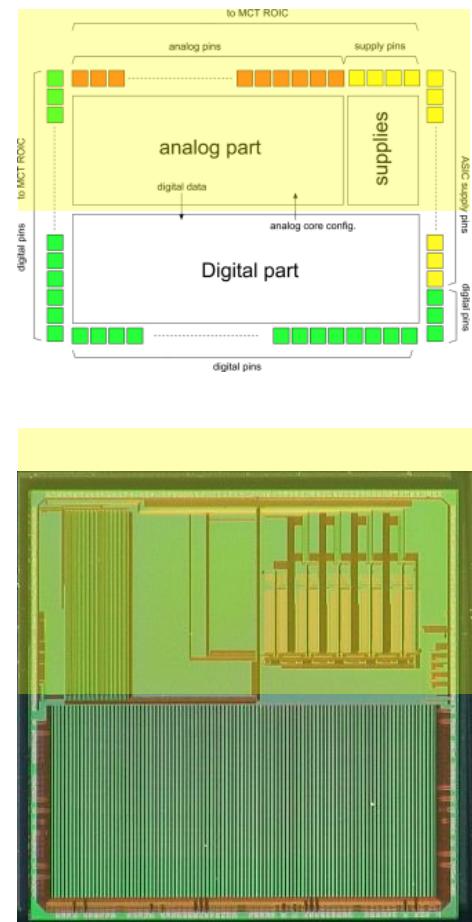
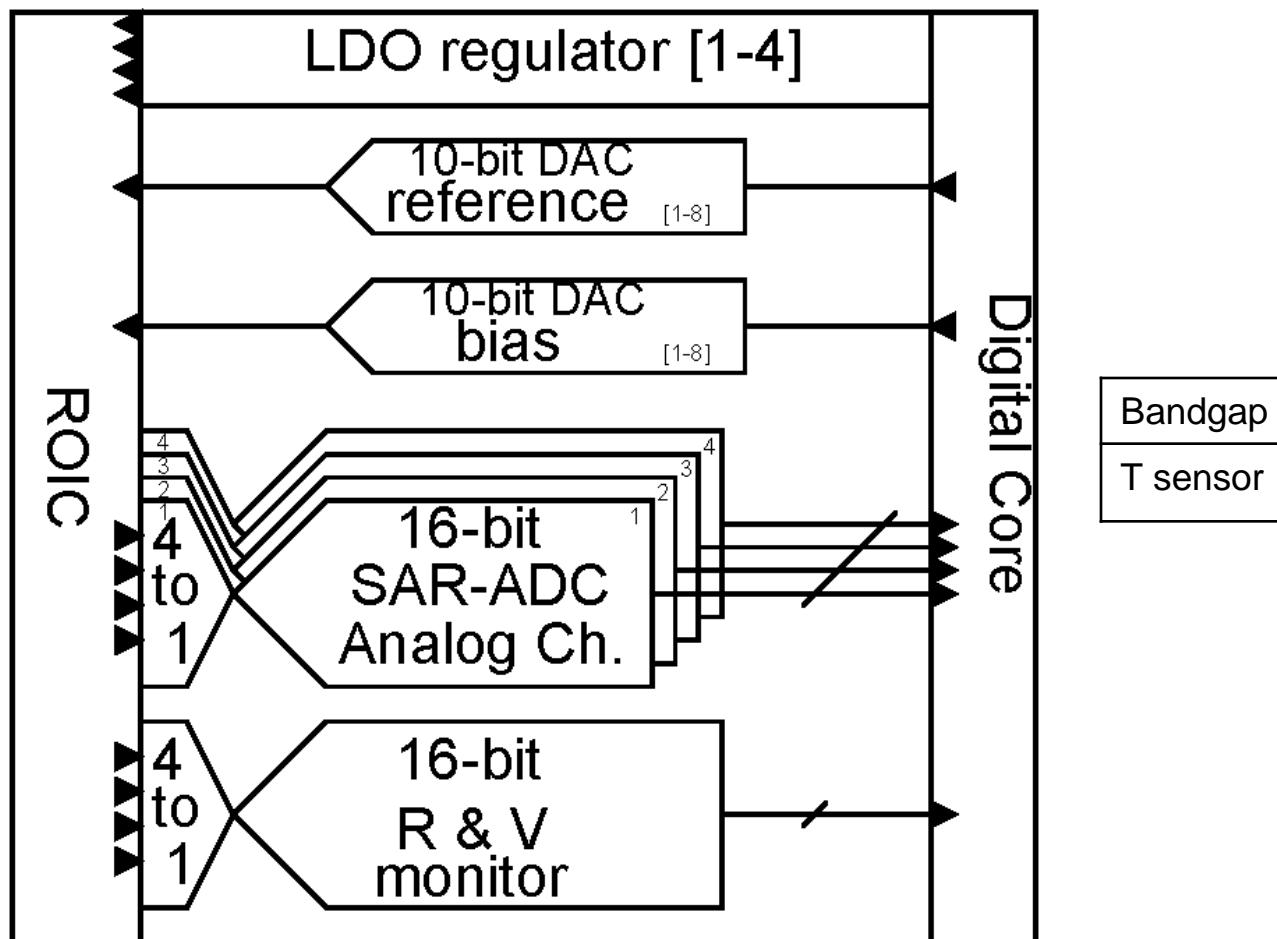
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# Architecture

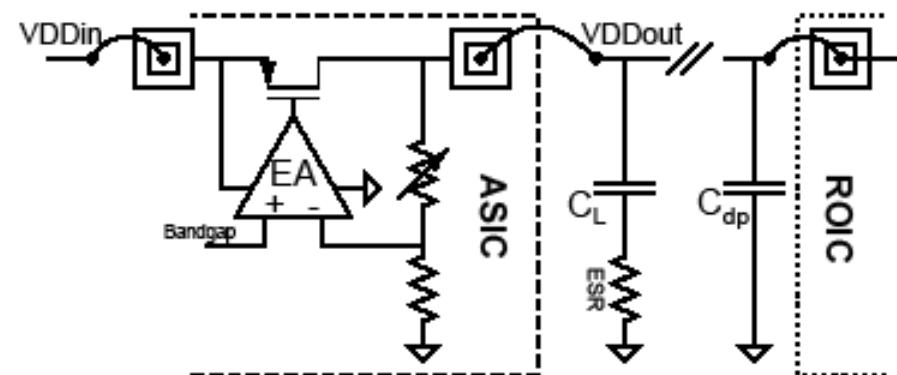
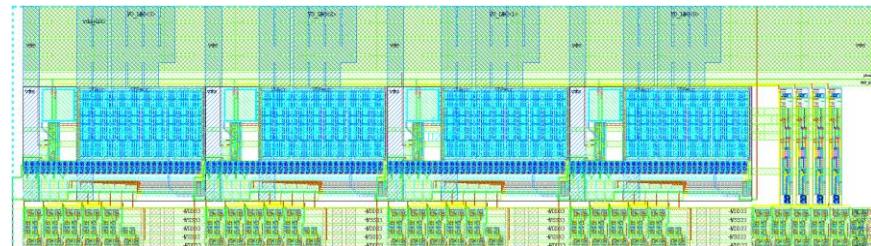


# Analog section



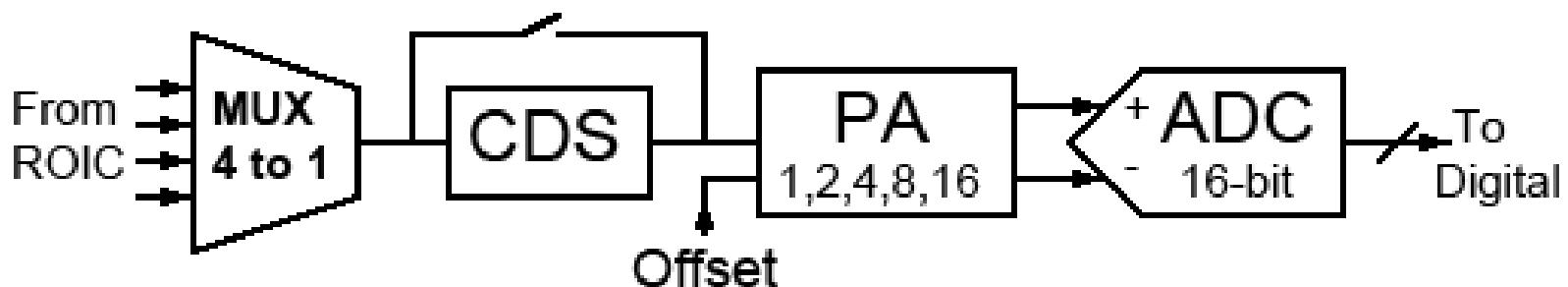
# Supply

- LDO
  - Programmable output
    - 1.3...3.4V
  - Stability: PM>60°
  - Output current 0-100mA
- Bandgap
  - 1.2V
  - 77K-300K



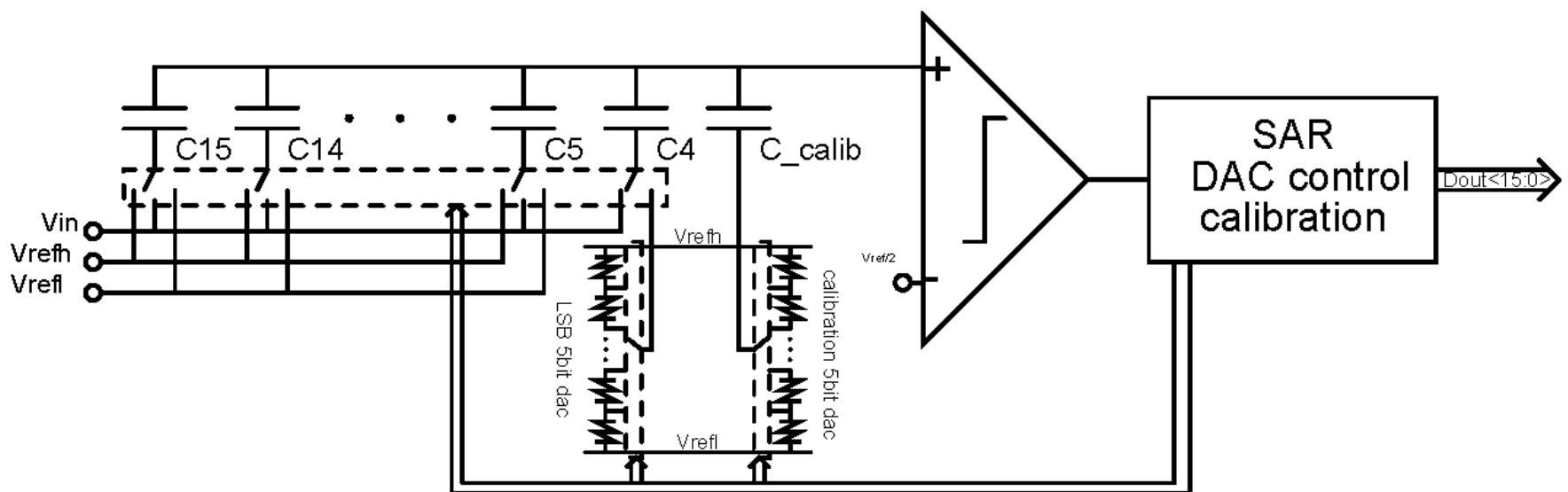
# Conversion channel

- One ADC addressed 4 analog inputs in prototype ASIC
- CDS
  - Bypassable
- Preamplifier (PA)
  - Programmable gain from 0-30dB in 6dB step
  - Offset cancellation (8-bit)
  - Single to differential

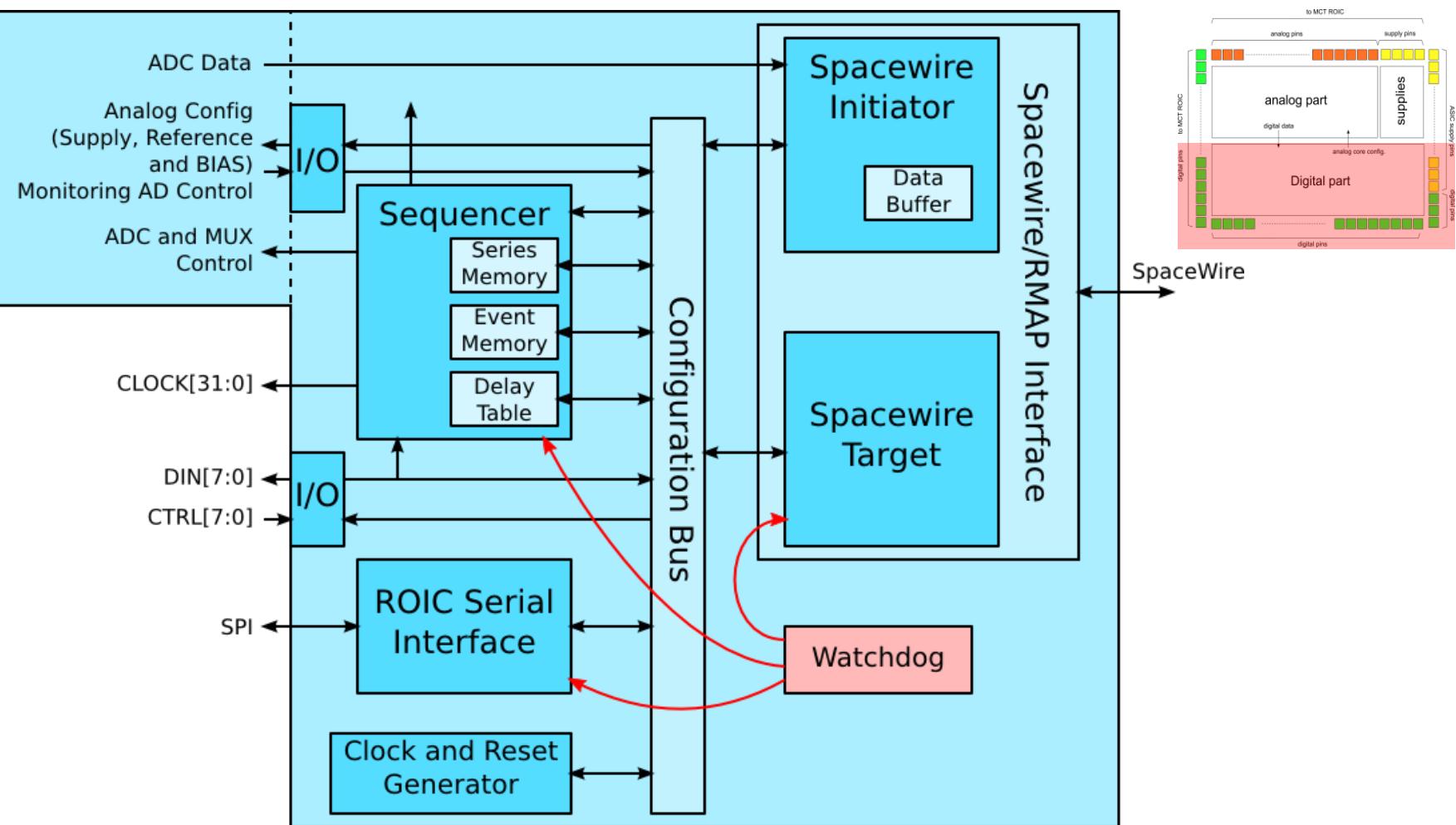


# ADC

- 16-bit, 100kHz, fully differential SAR ADC
  - Hybrid feedback DAC
  - Low offset comparator auto zero
- A calibration scheme is implemented

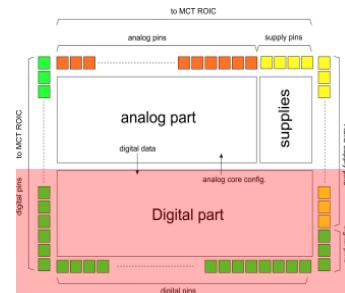


# Digital section



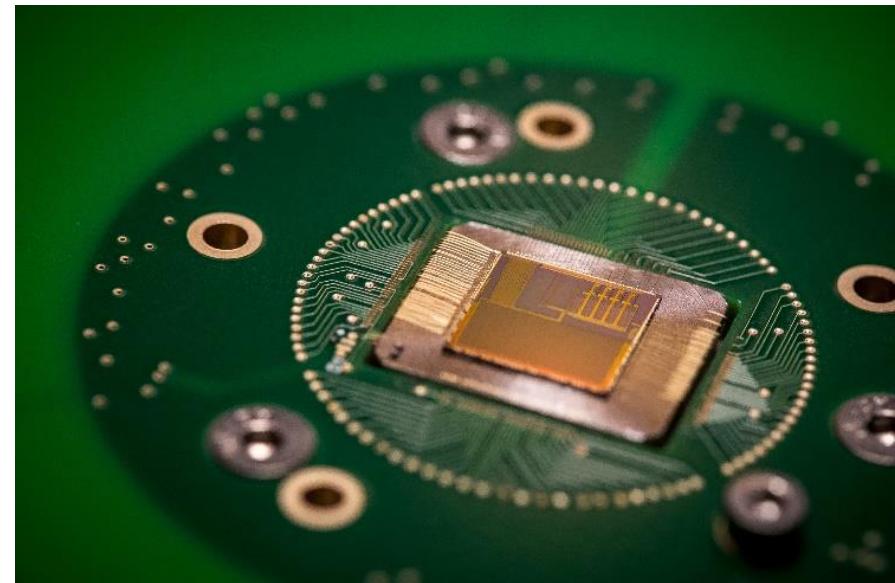
# Specifications

<b>Digital domain</b>	
Master clock	0 – 200 MHz
System level protocol	2 – 200 Mbit/s Space Wire
ROIC digital control	32
ROIC monitoring and trigger inputs	8
Scheduler time granularity	10M updates/s
Sequence nesting depth	8
ROIC programming channel	1 SPI



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# Radiation hardness: digital

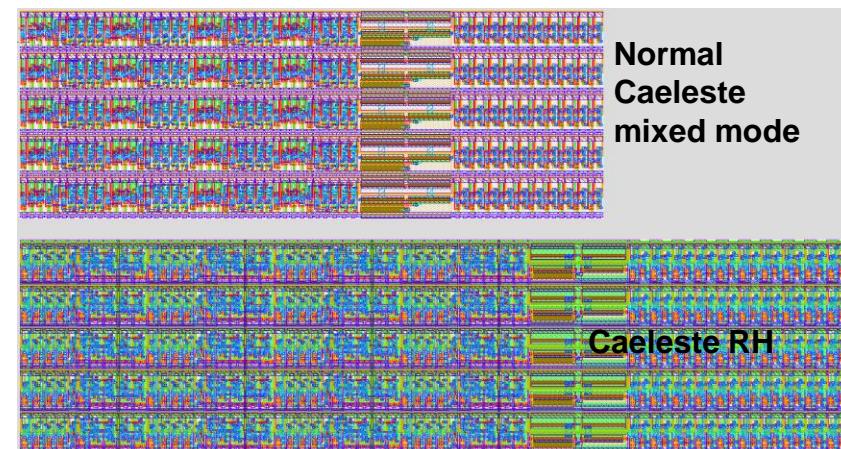
- Synthesized digital logic
  - DARE lib (IMEC & ESA)
    - 0.18 um CMOS 1P6M
    - Digital cell with TID, SEU, SEL tolerance
    - Allows custom mixed-signal design
  - Redundancy
    - Hamming Codes
    - Parity check
    - Safe FSMs
  - Watchdog Timers

# Radiation hardness: analog

DARE has a limited subset of analog component.

Caereste developed its own radhard cells

- Analog and High Voltage logic standard cells
- Full custom tactical cells
  - Analog & mixed mode
  - TID & TnID hardness
  - SEL hardness
  - SEU hardness without TR
  - <20% increased Cin and power
  - <50% area increase



# Design for low temperature

- Synthesized digital logic:

- A derating of speed, power, etc. of the library
- SRAM

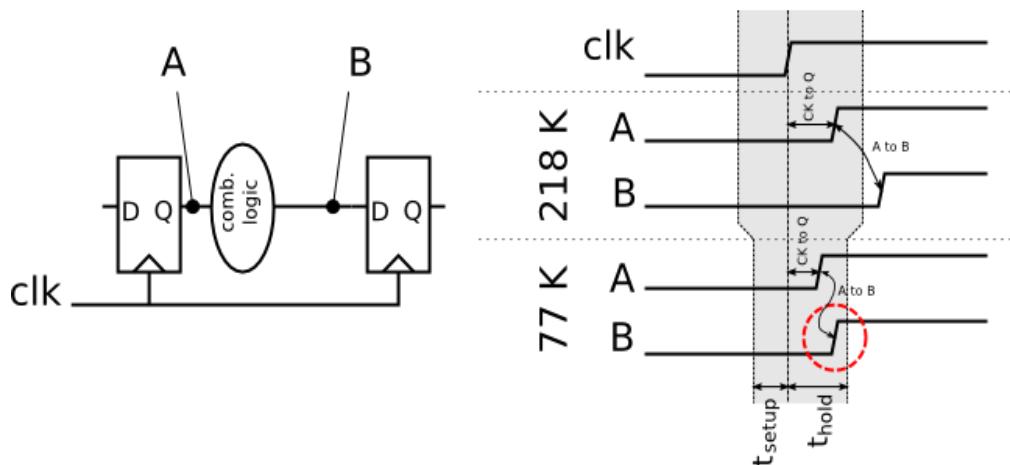
- Analog custom design:

- Active component modeling
- Component selection

# Cryogenic digital design

The DARE library has never been used at 77K before

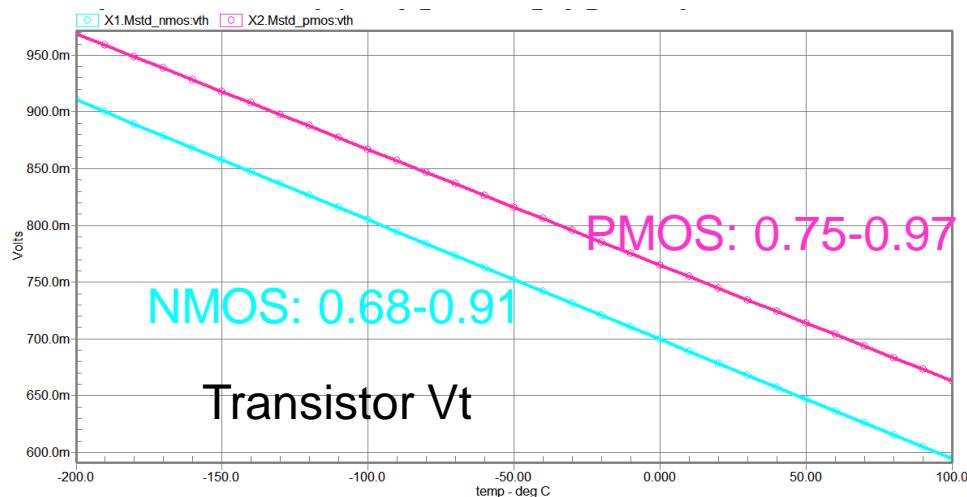
- Faster but risk for set-up and hold time violation.



- Adapted models based on characterization at 218K
- SRAM has not been validated before
  - Backup registers

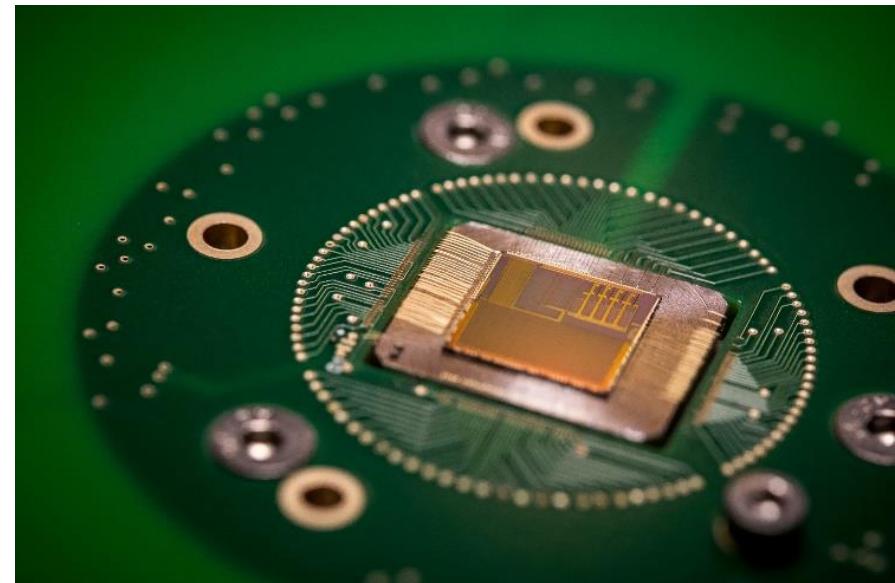
# Cryogenic analog design

- MOSFET modeling
  - $V_{th}$ : increase
  - Mobility: increase
  - MOS switch: low  $R_{on}$
- Passive components
  - Highly doped non silicide poly Resistor for stability
  - MIM capacitors
- Rely on ratios not absolutely values



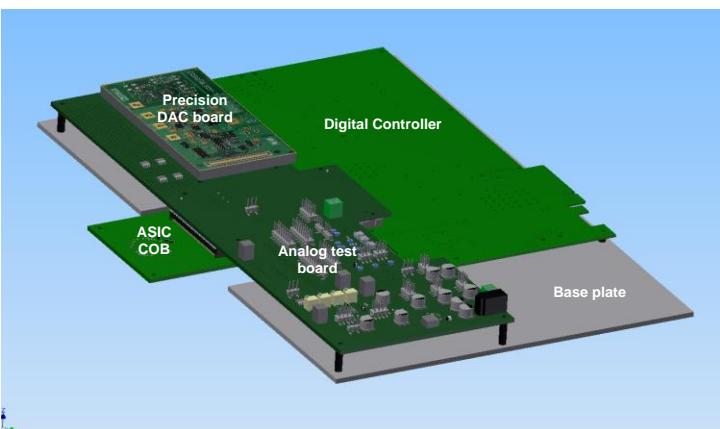
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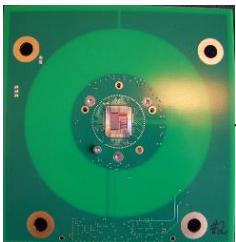


# Test setup

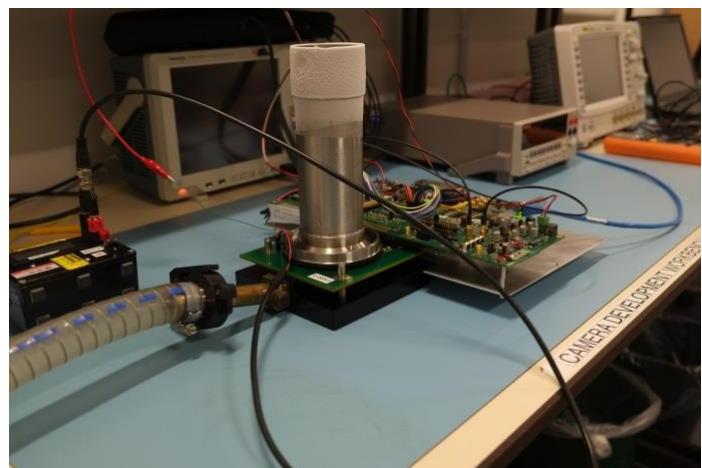
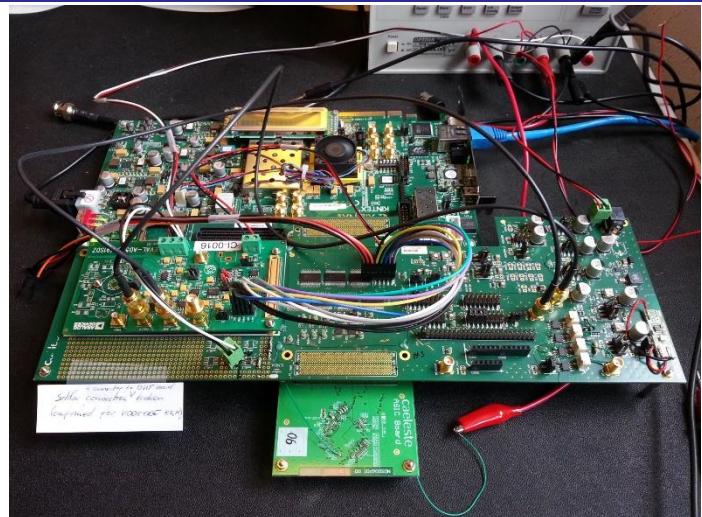
Unified design for:  
RT board  
CT board



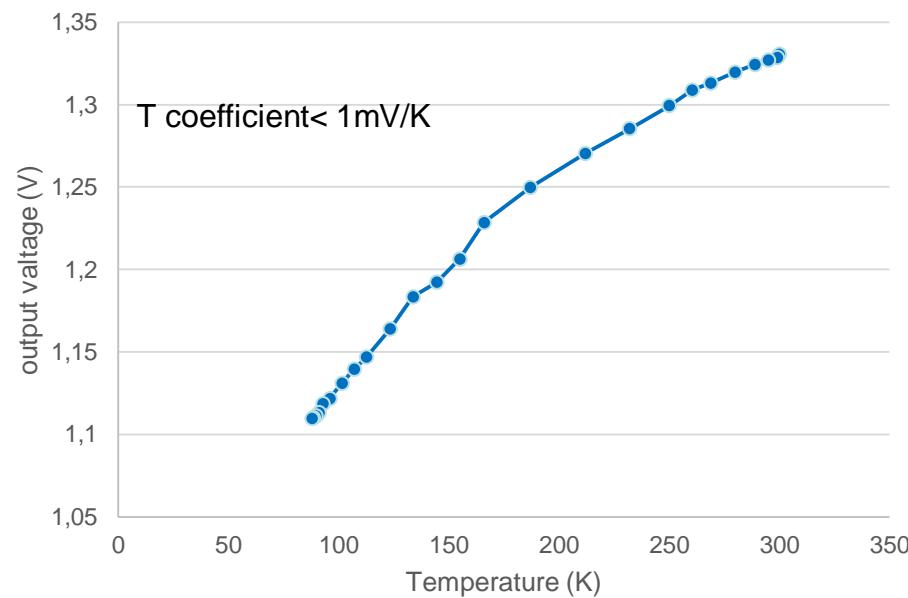
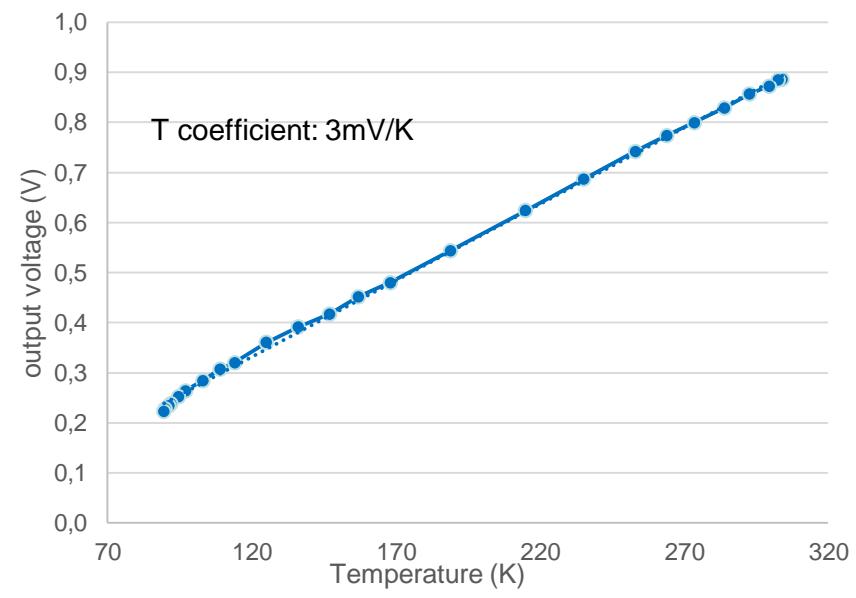
RT board



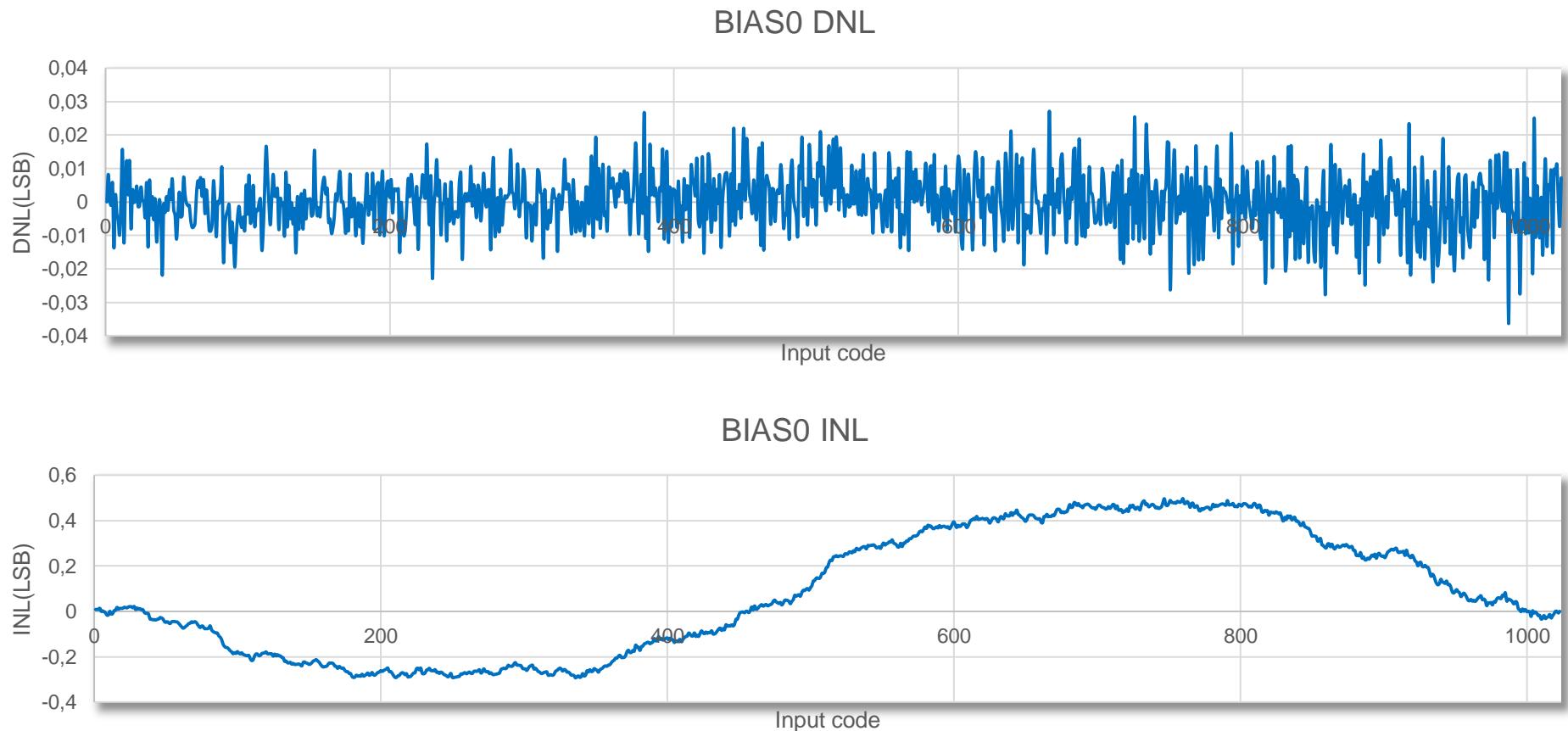
CT board



# Bandgap and temperature sensor

**Bandgap measurement****T-sensor measurement**

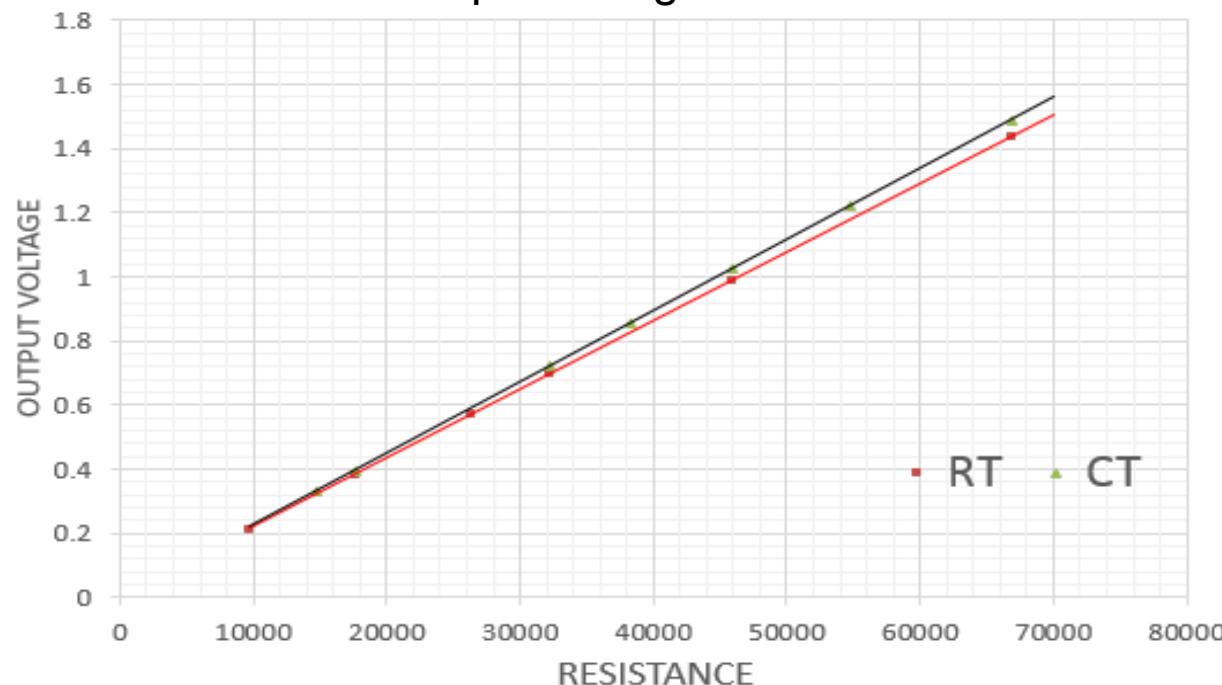
# Reference and Biases 10-bit



# R monitor

- **On chip SC current source.**
  - R range 10k – 70k ohm

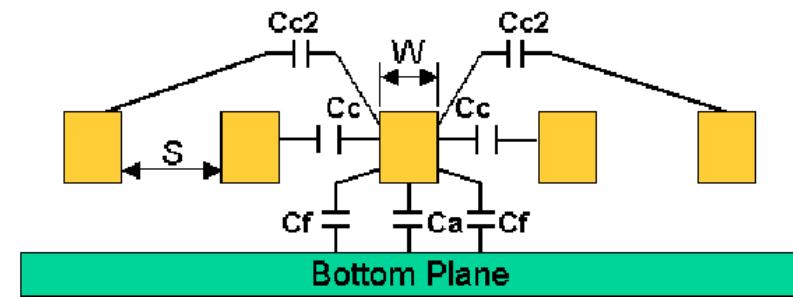
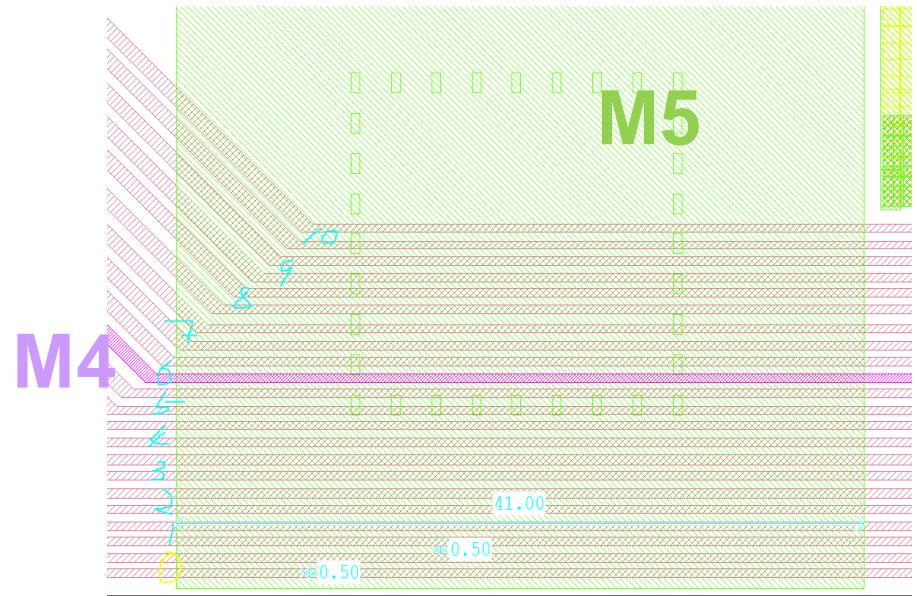
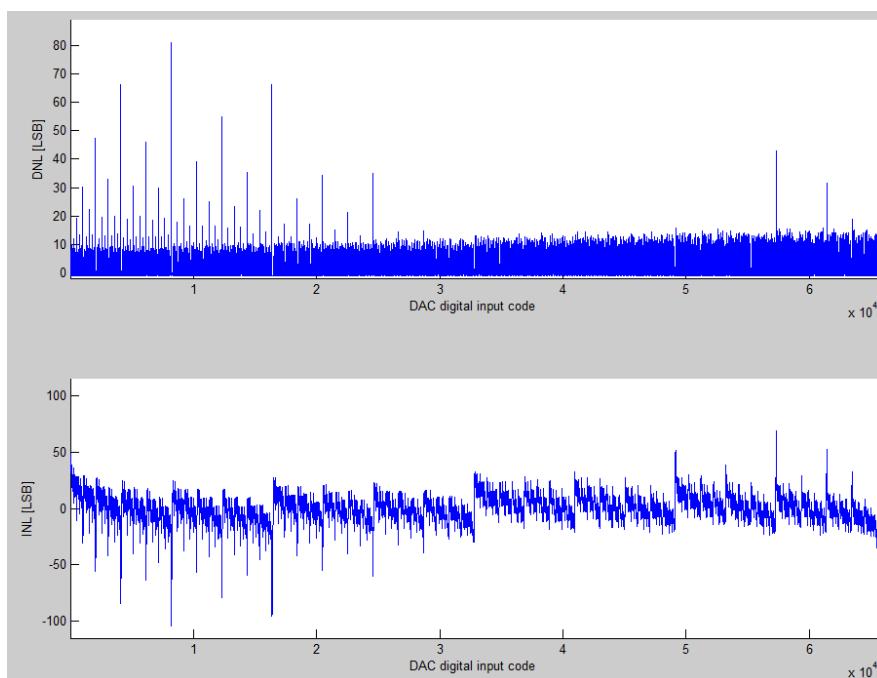
Measured output voltage with 2MHz clock



# 16-bit SAR ADC INL DNL

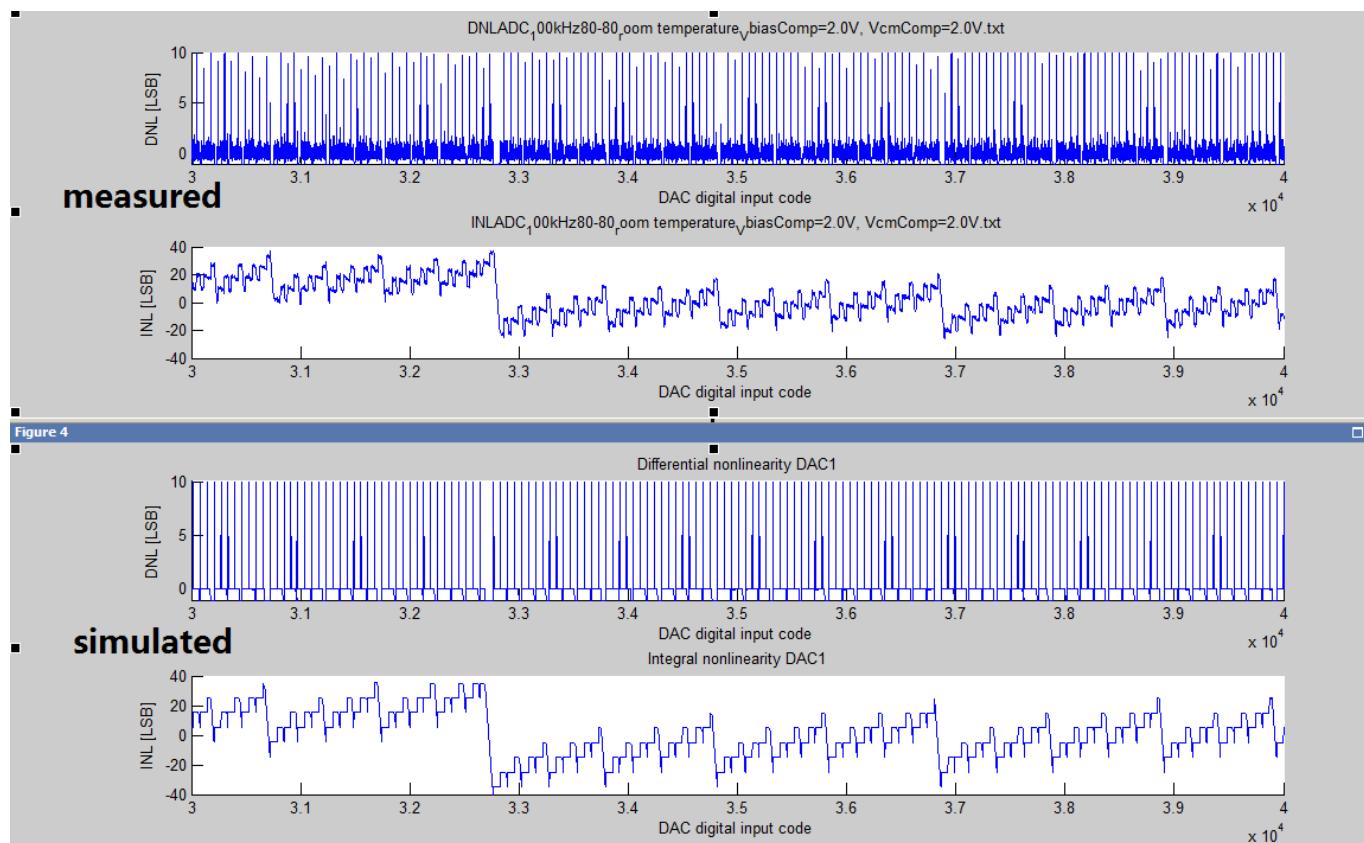
## •INL DNL problem :

–Root cause is a AC coupling in the  
**layout: 2 fF cross-coupling**



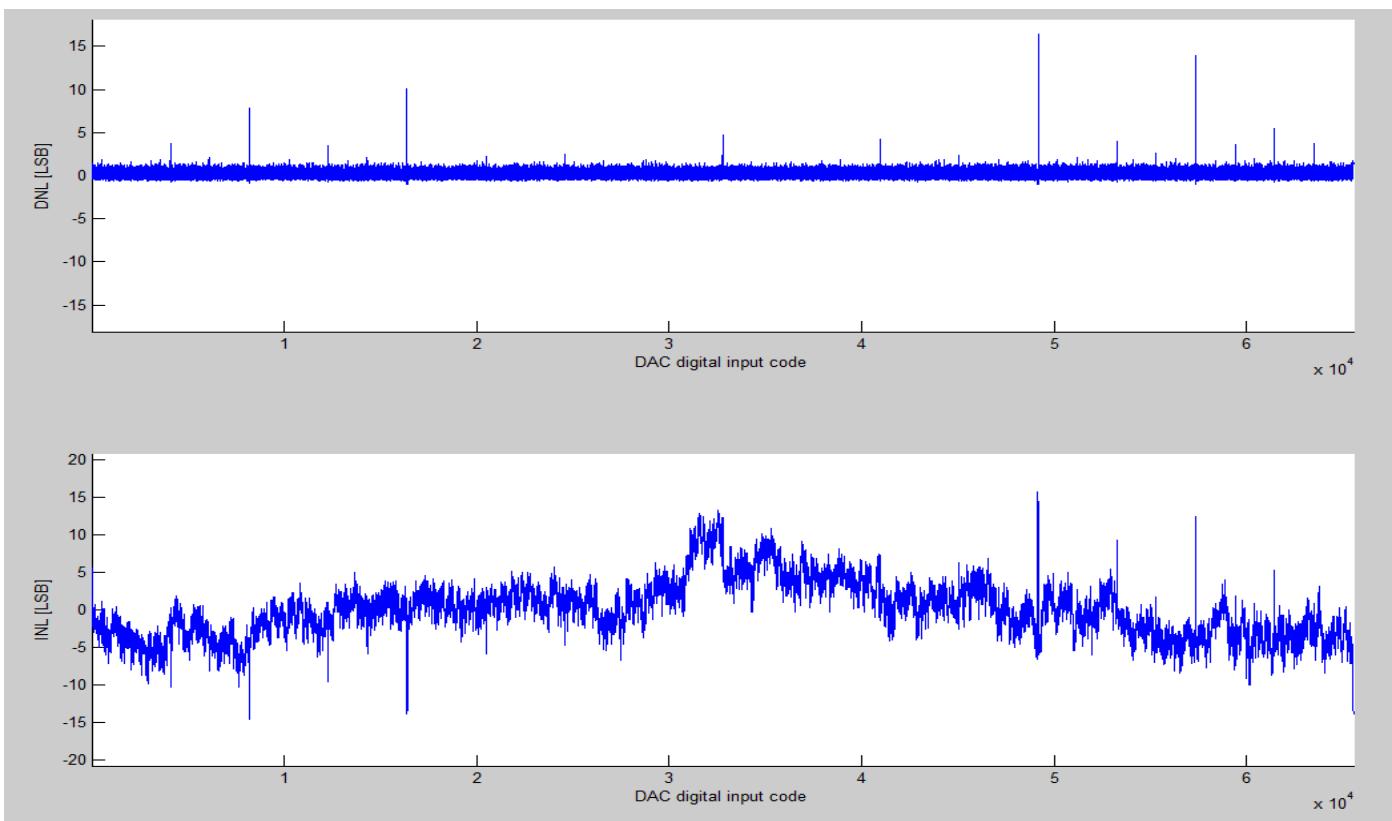
# ADC INL DNL

- **ADC INL DNL problem analysis**



# ADC INL DNL

- **ADC INL DNL @ 50KHz fs**

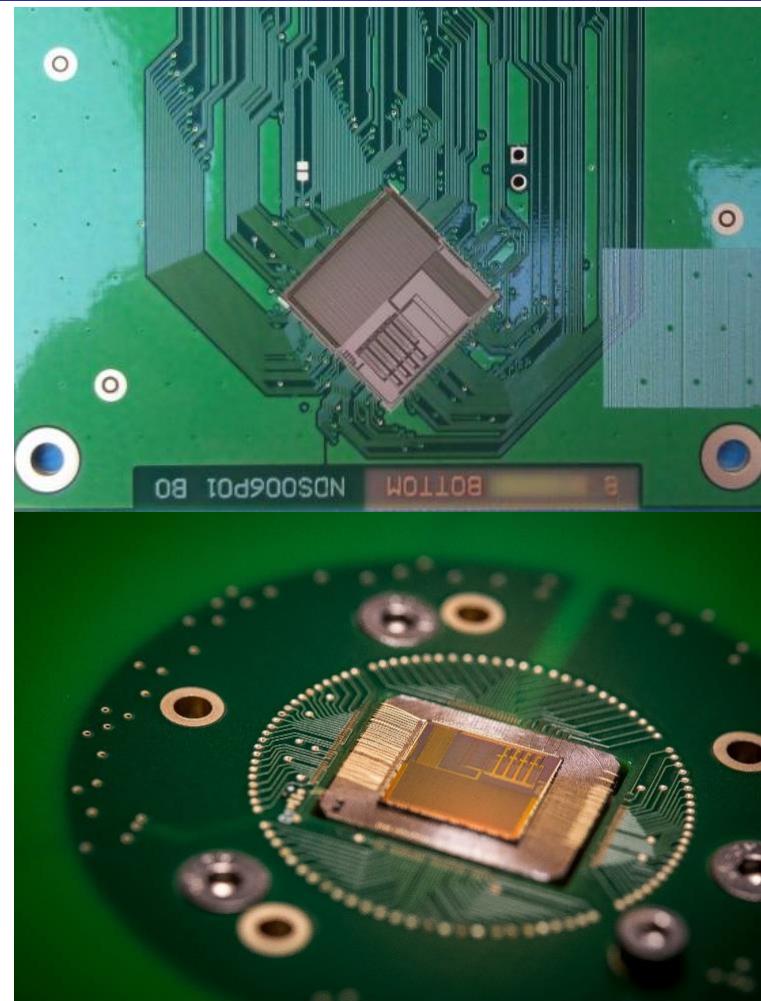


# Measurement summary

Specs	Measurement result @ room T	@ cryogenic T
Supply voltage	3.5-3.6V	
Total current consumption	53mA	60.5mA
Regulator PSRR	> 40dB	
Regulator I out	> 40mA	
Output impedance	< 1Ω	
LDO output	1.3-3.4 V	
Analog rail to rail voltage	3.3 V	
Reference DAC INL	0.7LSB	1LSB
Reference DAC DNL	0.06LSB	0.04LSB
ADC noise	2.5LSB	2.1LSB
ADC fs	50, 100, 200KHz	
ADC INL	78LSB (15LSB@50KHz)	
ADC DNL	76LSB (16LSB@50KHz)	
Monitor resistance range	10KΩ -70KΩ	
Number of digital outputs/ inputs	32 / 8	
Digital output clock speed	0-10 MHz	
Serial interface speed	50KHz-50MHz	
SpaceWire bit rate	0-200 Mbps	
ASIC start-up time	≤50us	
Temperature range	77K-room T (Measured)	

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# Conclusions

- Prototype accompany ASIC for (IR) detector arrays which provide all functionalities has been demonstrated
  - ADC problem founded and will solve in next iteration
- Full function has been proven from cryogenic (77K) to room temperature
  - All Caereste custom designed cells
  - Digital cells in DARE Lib. Including SRAM
- Highly flexible for ROICs
  - Highly programmable sequencer
  - Wide programmability and large dynamic ranges in analog acquisition chain
- Beyond IR imagers

# Next steps ?

- Larger ASIC with multiple channels (32 to 64)
- Faster ADCs is now developing at Caeleste (up to 12MS/s with reduced resolution)
- Irradiation testing
- More discussion with instrument builders and IR sensor manufacturers for further enhancements

# Thank you!

